

Università degli Studi di Trieste
Dipartimento di Ingegneria e Architettura
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Scienza e Tecnologia dei Materiali Ceramici

Modulo 2: Materiali Nanostrutturati

- Lezione 4 -

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5 μm

Previous lecture: Review

- Basic nanostructures: overview
- Nanoparticles
 - Stabilization approaches

This lecture: Content

- Basic nanostructures: overview
- Nanoparticles
 - Steric stabilization approaches
 - Colloidal synthesis of nanocrystals of binary compounds
 - Colloidal synthesis of metal nanoparticles
 - Kinetics of nucleation and growth in colloidal suspensions
 - Optoelectronic properties
 - Applications

Where are we?

3. Fabbricazione

- Approcci “bottom-up”:
 - **Building blocks (nanocristalli:** wells and films, wires, dots; carbon based nanostructures: fullerenes, graphenes, etc.)
 - Proprietà dei building blocks
 - **Metodi di fabbricazione** (depositioe di film, aerosol, sospensioni colloidali, epitassia controllata, etc.)
 - Assemblaggio (self assembly bioassistito, self assembly via polimeri, eterostrutture, Marangoni, ...)
- Approcci “top-down”
 - Litografia, ball milling, ion implantation, thin film layers + thermal treatment, etc.

5 μm

Approaches to nanoparticle synthesis

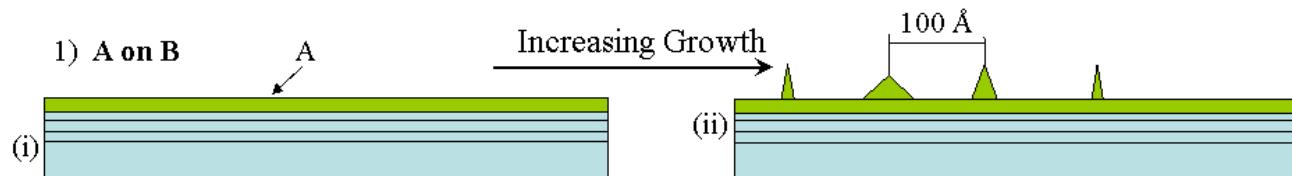
Nanoparticles: nano-sized particles, crystalline or amorphous (1-200 nm)

Nanocrystals: single crystal nanoparticles

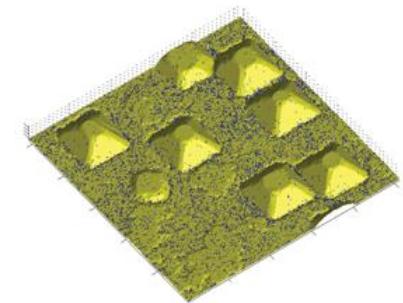
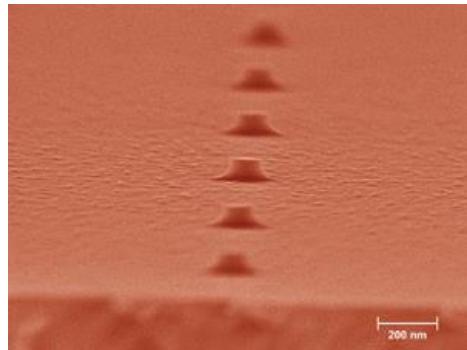
Quantum dots: nanoparticles where quantum confinement effects are important

Approaches to nanoparticle synthesis

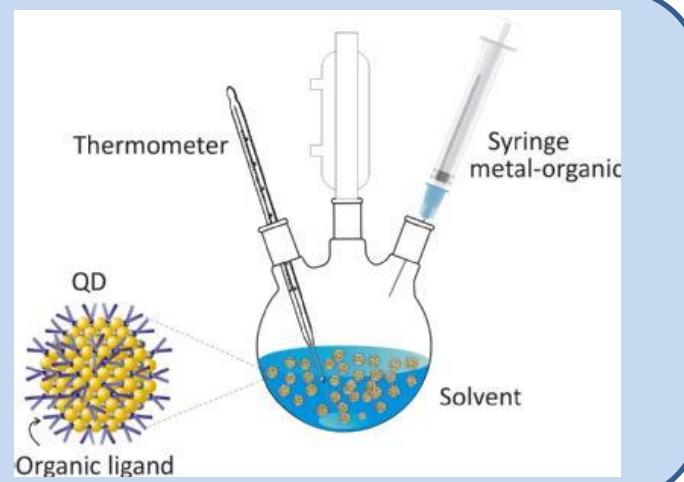
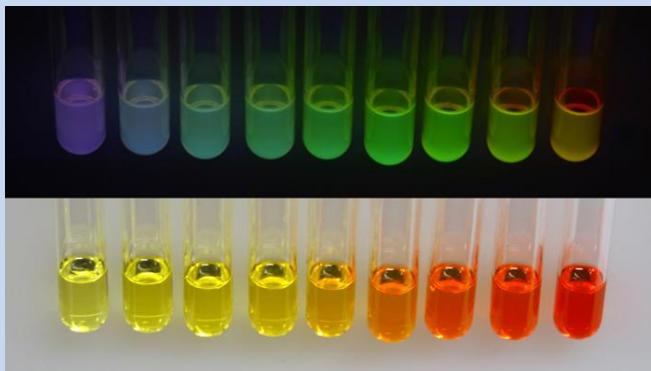
- Self-assembled nanocrystals



- Lithography



- Colloidal nanocrystals



Example: Colloidal synthesis of CdSe

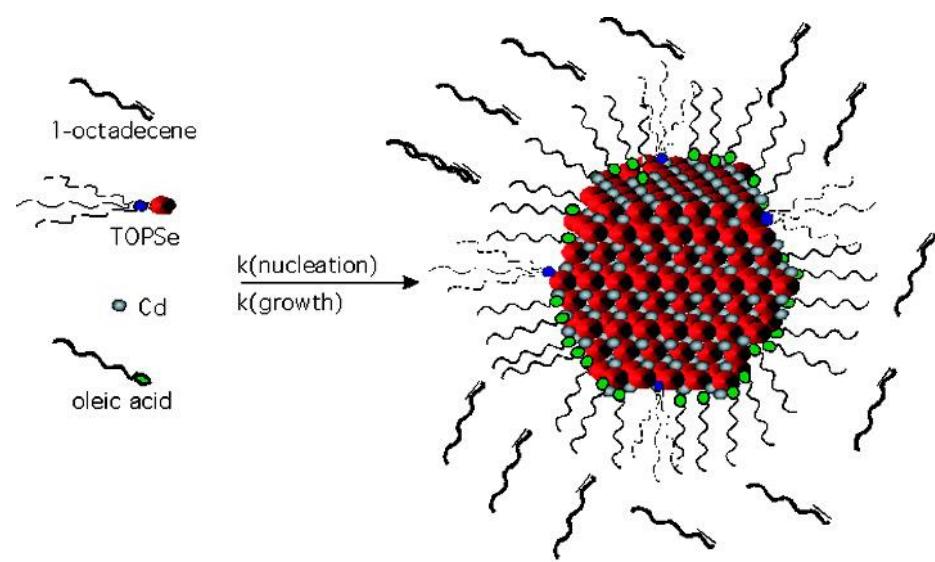
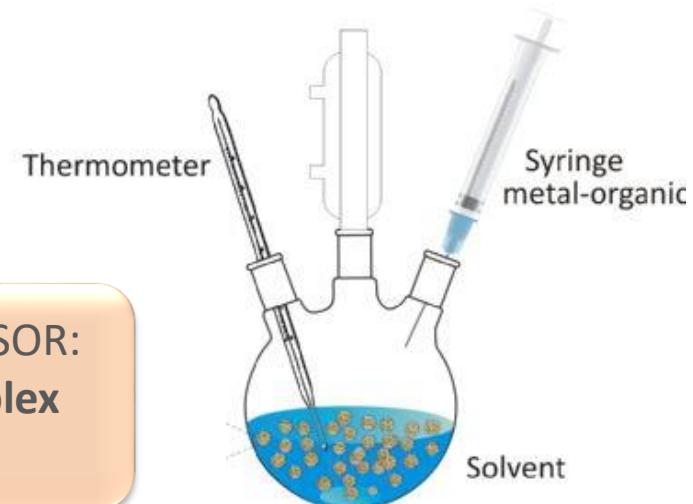


CADMUM PRECURSOR:
Oleic Acid +
Cadmium complex
in solvent

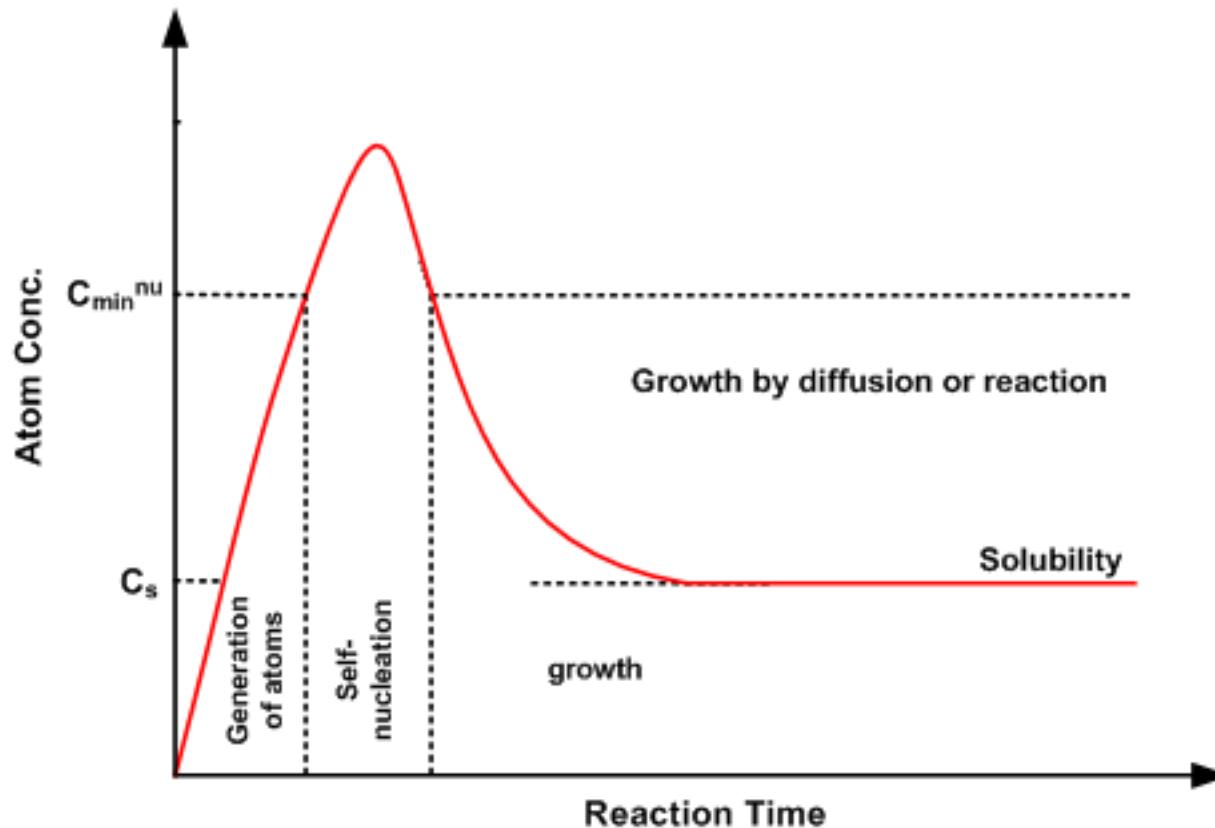
SELENIUM PRECURSOR:
TOP-Selenio complex
in solvent

mixing

CdSe precipitation



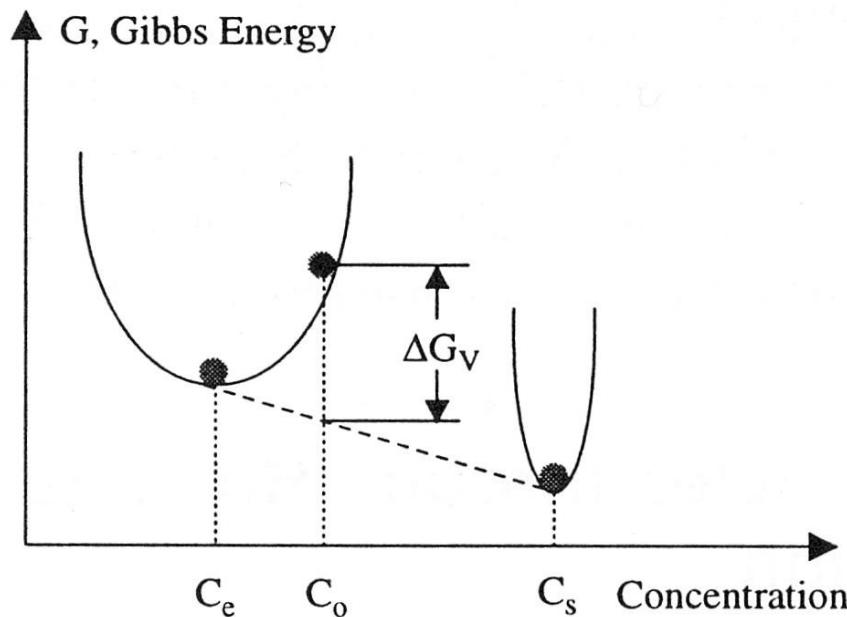
Synthesis of nanoparticles: Time evolution of concentration profile



Driving force

Supersaturation → High G

ΔG : driving force for nucleation and growth



Supersaturation

ΔG_v per unit volume in solid phase:

$$\Delta G_v = -\frac{kT}{\Omega} \ln(C/C_0) = -\frac{kT}{\Omega} \ln(1 + \sigma)$$

C: solute concentration

C_0 : equilibrium concentration (solubility)

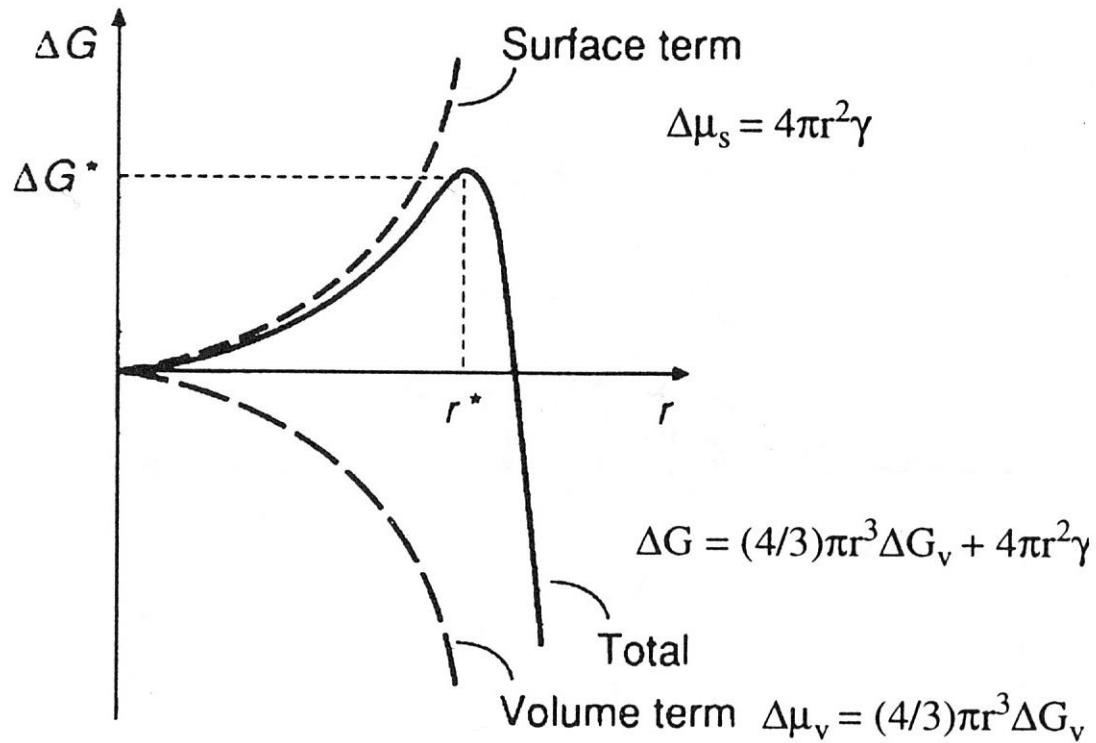
k: Boltzman, Ω è il volume atomico, e

σ : supersaturation defined as $(C-C_0)/C_0$.

No supersaturation ($s=0$) $\rightarrow \Delta G_v = 0 \rightarrow$ no nucleation

If $C > C_0$ ($s > 0$) $\rightarrow \Delta G_v < 0 \rightarrow$ nucleation

Homogeneous nucleation



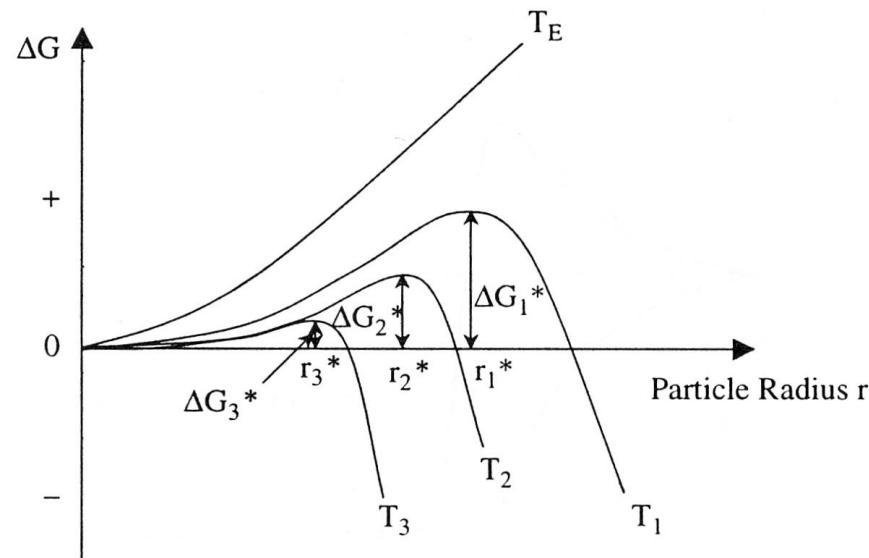
$$r^* = -2 \frac{\gamma}{\Delta G_v}$$

$$\Delta G^* = \frac{16\pi\gamma}{(3\Delta G_v)^2}$$

Homogeneous nucleation

$$r^* = -2 \frac{\gamma}{\Delta G_v}$$

Critical radius: minimum size attainable



Factors influencing r^* :

- $\Delta G_v \rightarrow$ supersaturation
- Surface energy \rightarrow
 - Temperature
 - System chemistry (solvent, etc.)

Homogeneous nucleation

Rate of nucleation:

$$R_N = nP\Gamma = \left\{ \frac{C_o kT}{3\pi\lambda^3\eta} \right\} \exp\left(-\frac{\Delta G^*}{kT}\right)$$

$$P = \exp\left(-\frac{\Delta G^*}{kT}\right)$$

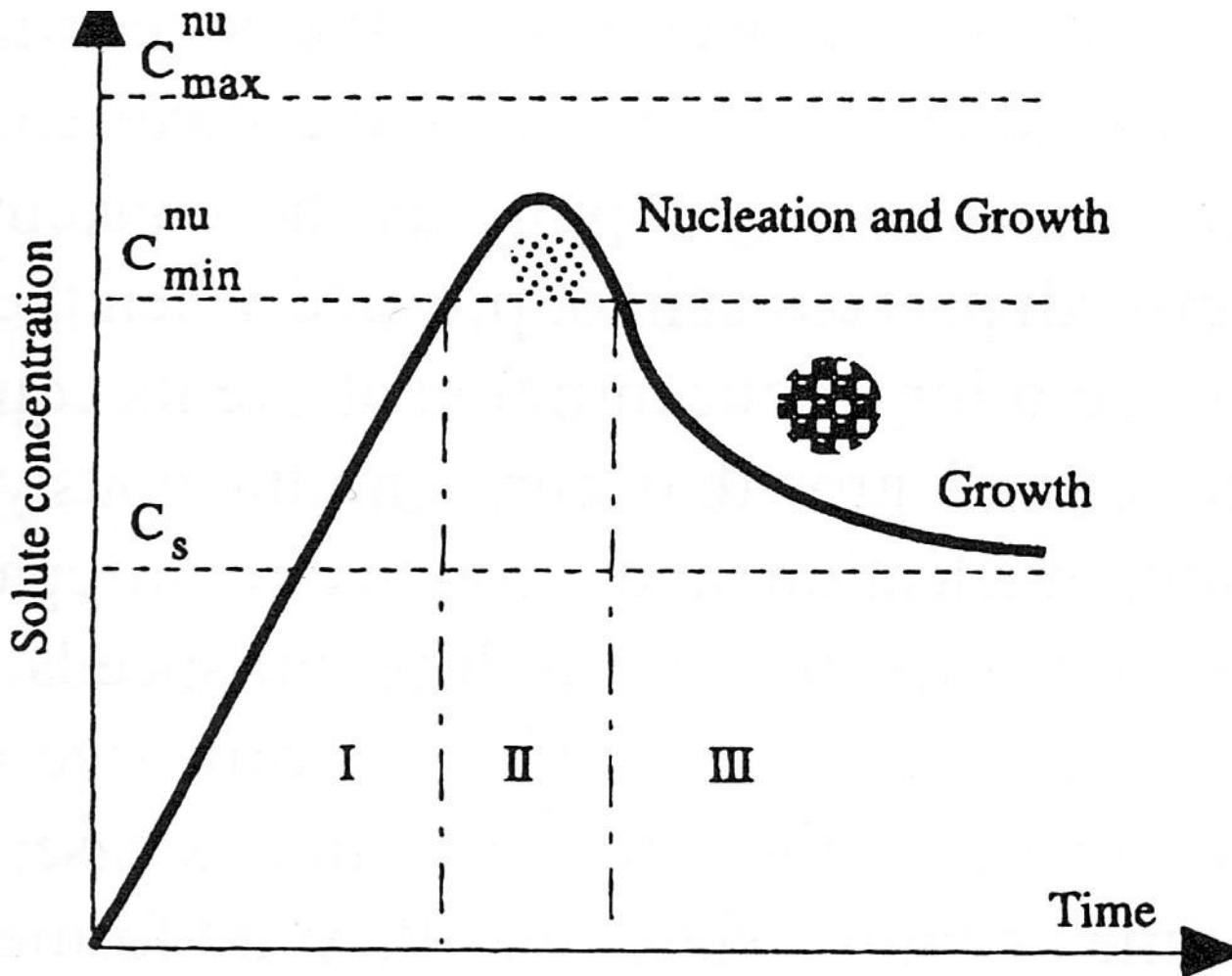
$$\Gamma = \frac{kT}{3\pi\lambda^3\eta}$$

- n: number of species in solution per unit volume; (in homogeneous nucleation = C_0)
- λ : diameter of growth species
- η : viscosity of the solution

Large amounts of nuclei are favored by:

- High C_0
- High temperature
- Low viscosity
- Low ΔG^*

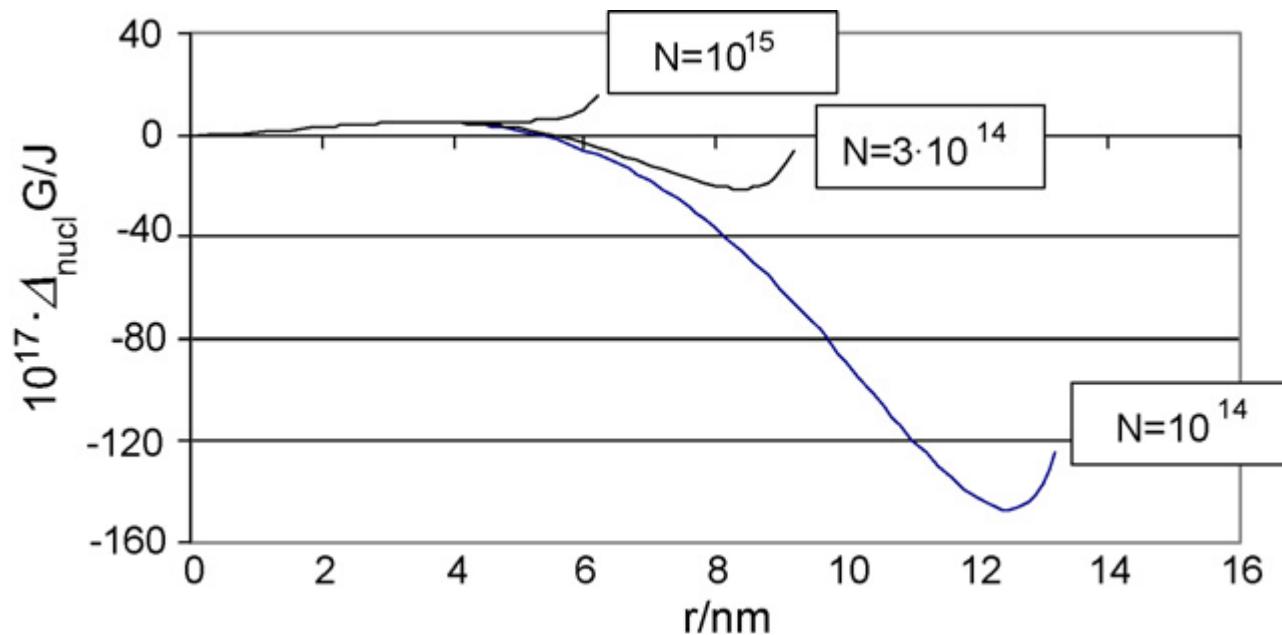
Homogeneous nucleation



Modified homogeneous nucleation

$$\Delta G = 4\pi r^2 \gamma_s + \frac{4}{3}\pi r^3 \Delta G_v$$

$$\Delta G_v = -\frac{RT \ln S_{CdSe}}{V_{mol}}$$



Modified homogeneous nucleation

$$\Delta G = 4\pi r^2 \gamma_s + \frac{4}{3}\pi r^3 \Delta G_v$$

$$\Delta G_v = -\frac{RT \ln S_{CdSe}}{V_{mol}}$$

$$C_{CdSe} V_{tot} = C_{CdSe\ 0} V_{tot} - n_{CdSe\ np}$$

cioè le moli di monomero in soluzione saranno quelle iniziali diminuite delle moli di CdSe nelle particelle. Queste vengono valutate mediante

$$n_{CdSe\ np} = \#_{np} \left(\frac{4}{3}\pi r^3 \right) \frac{\rho_{CdSe}}{MW_{CdSe}}$$

il numero di nanoparticelle si ricava dalla nucleation-rate

$$R_n(t) \propto \exp \left(-\frac{1}{T^3 \ln^2 S(t)} \right)$$

$$\#_{np} = \sum_{t=0}^{end} R_n(t)$$

In alcuni casi, di ha una decrescita delle particelle. Quando la dimensione di queste raggiunge lo zero (regolata dalla growth-rate), il numero di nuclei viene ridotto.

La growth-rate invece deriva da

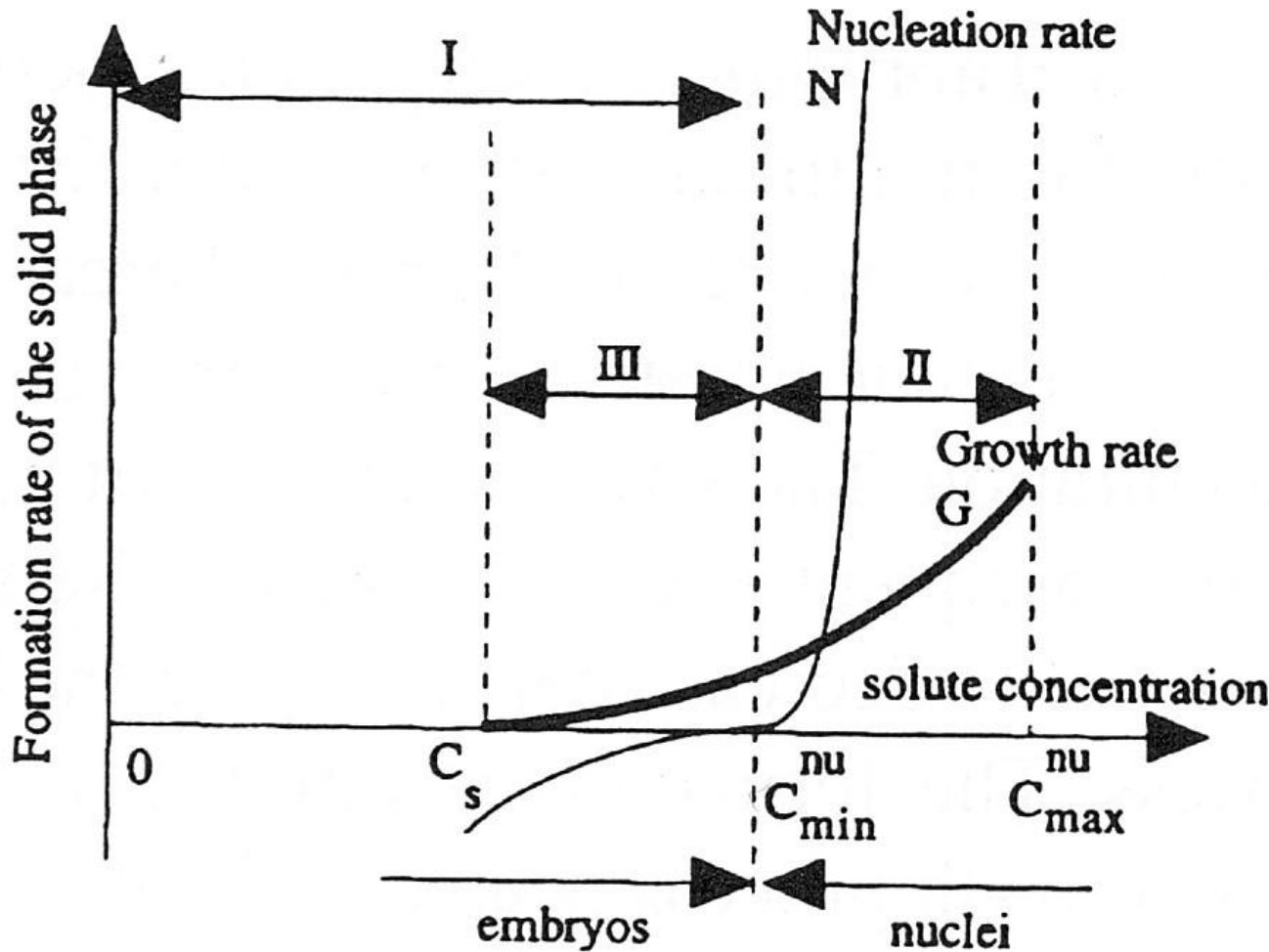
$$\dot{r} = \frac{dr}{dt} \propto \frac{1}{rr_c} - \frac{1}{r^2}$$

I due contributi all'energia libera (superficiale e volumetrico) quindi possono venire espressi dall'equazione

$$\Delta G_{np} = 4\pi r^2 \gamma_s - \frac{4\pi r^3 RT}{3 V_m} \ln \left(S_{CdSe\ 0} - \#_{np} \left(\frac{4}{3}\pi r^3 \right) \frac{\rho_{CdSe}}{MW_{CdSe} C_{sol} V_{tot}} \right)$$

Va integrata su r. tutte le volte che vedo r in realtà dovrebbe essere l'integrale

Homogeneous nucleation



Growth

Growth of nuclei: two steps

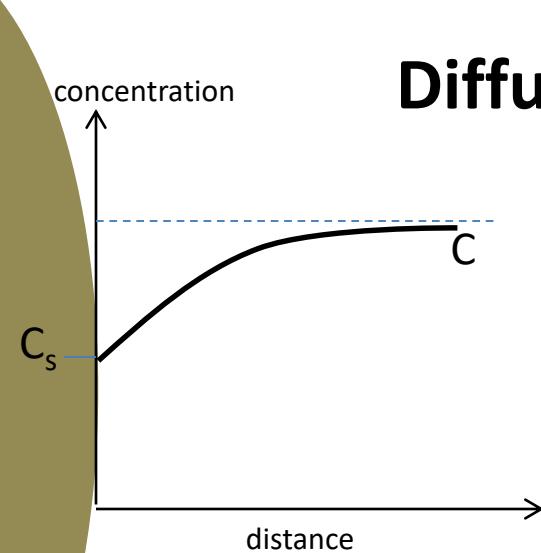
1) Diffusion

- Growth-species generation
- Migration of growth-species to nuclei surface
- Adsorption of growth-species to nuclei surface

2) Growth (irreversible incorporation of growth species into the surface)

Growth

Diffusion-controlled growth:



$$\frac{dr}{dt} = D(C - C_s) \frac{V_m}{r}$$

r: particle radius
V_m: monomer volume
D: diffusion coefficient

$$\rightarrow r^2 = 2D(C - C_s)V_m t + r_o^2$$

$$\rightarrow \delta r = \frac{r_o \delta r_o}{\sqrt{k_D t + r_o^2}} \quad \text{where} \quad k_D = 2D(C - C_s)V_m$$

As growth proceeds, size dispersion gets better

Diffusion-controlled growth favors the formation of uniformly dispersed particles

Growth

Growth controlled by surface processes:

Concentration of growth species is the same on the surface as in the bulk

Mononuclear growth (layer by layer): $\frac{dr}{dt} = k_m r^2$ (growth proportional to surface area)

$$\rightarrow \frac{1}{r} = \frac{1}{r_o} - k_m t$$

As growth proceeds, size dispersion gets worse

$$\rightarrow \delta r = \frac{\delta r_o}{(1 - k_m r_o t)^2}$$

Polynuclear growth

(multiple layers grow simultaneously):

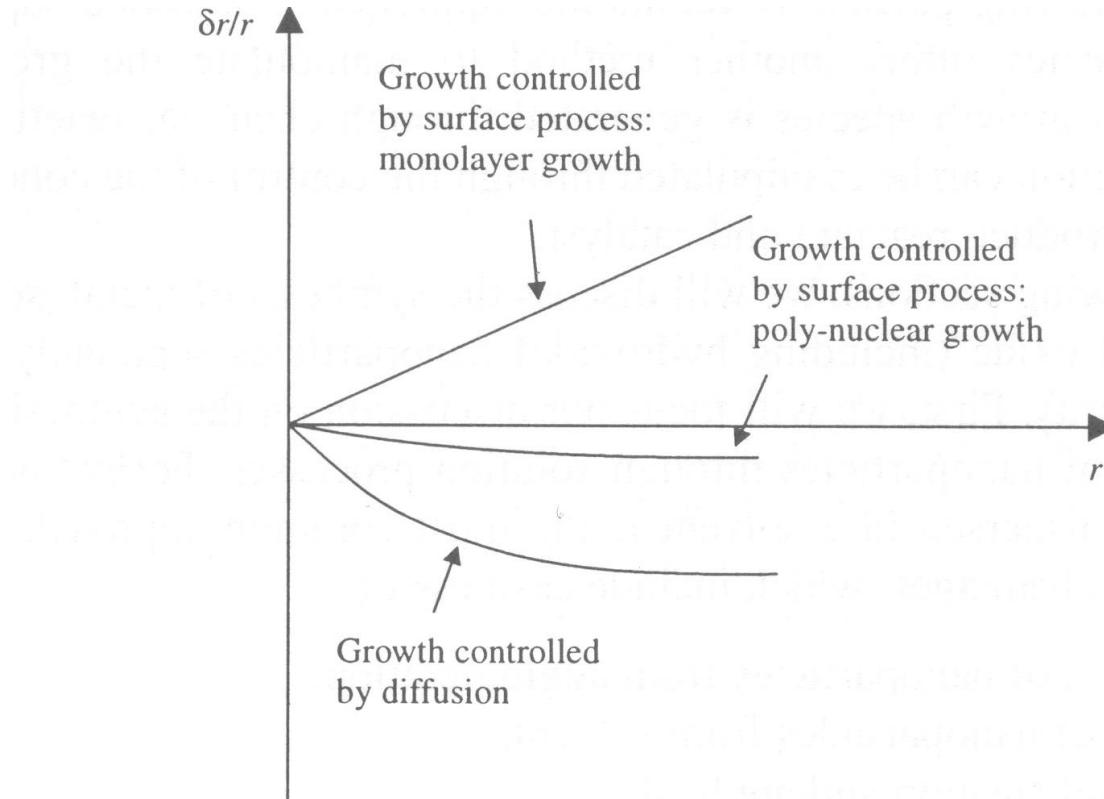
$$\frac{dr}{dt} = k_m \quad (\text{constant growth rate})$$

$$\rightarrow r = k_p t + r_o$$

$$\rightarrow \delta r = \delta r_o$$

As growth proceeds, size dispersion stays constant

Growth



To obtain monodispersed nanoparticles:
Use diffusion-controlled growth via:

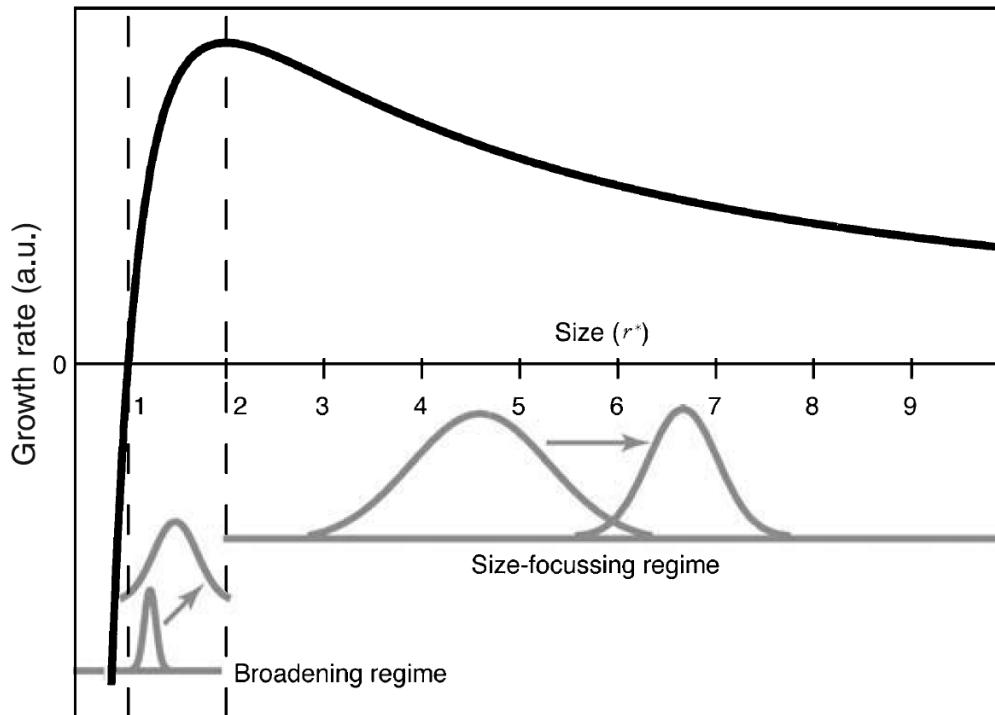
- low concentration
- high viscosity
- diffusion barrier at the surface
- controlled supply via chemical reactions

Growth: Diffusion-controlled regime + Size-induced dissolution

$$\frac{dr}{dt} = \frac{2\gamma DC_\infty \Omega^2}{k_B T} \frac{1}{r} \left(\frac{1}{r^*} - \frac{1}{r} \right)$$

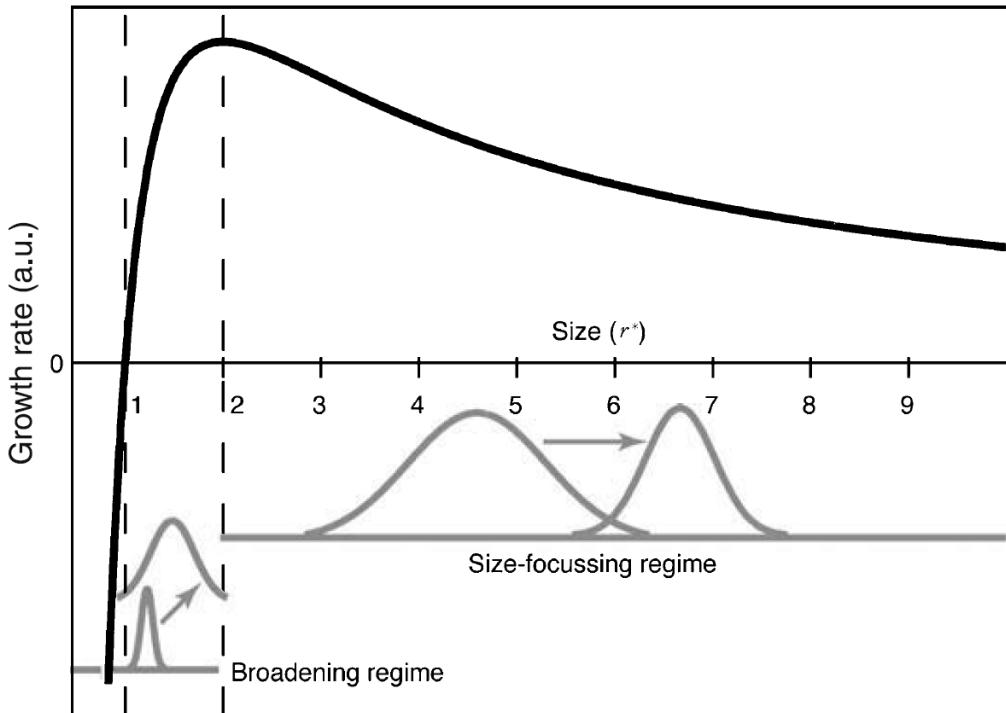
Derives from the diffusion-limited growth regime, considering Gibbs-Thompson

γ	surface energy
D	diffusion coefficient
C_∞	bulk solubility
Ω	monomer volume
r^*	critical radius



Size distribution control

- focusing and defocusing -



As synthesis proceeds:
Monomer concentration decreases
→ Critical radius increases

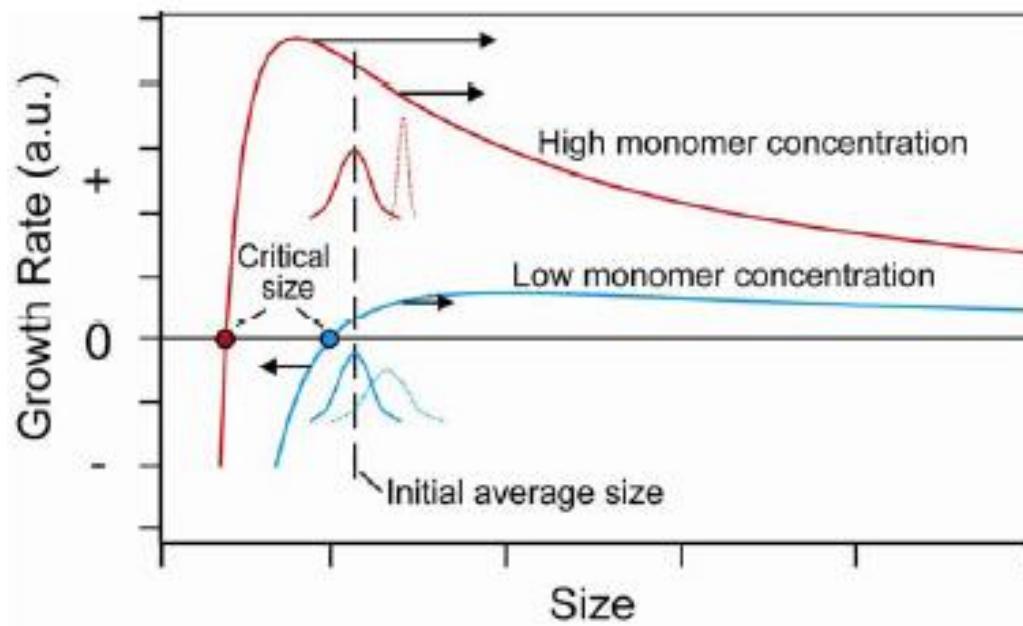
→ Growth regime evolves:

- Focusing $r_{\min} > 2r^*$
- Broadening $r_{\min} < 2r^*$
- Ostwald ripening $r_{\min} < r^*$

r_{\min} : radius of the smallest particle in the distribution

Size distribution control

- focusing and defocusing -



High monomer concentration (early synthesis stage):

Small critical size, all particles grow, small particles grow faster → focusing

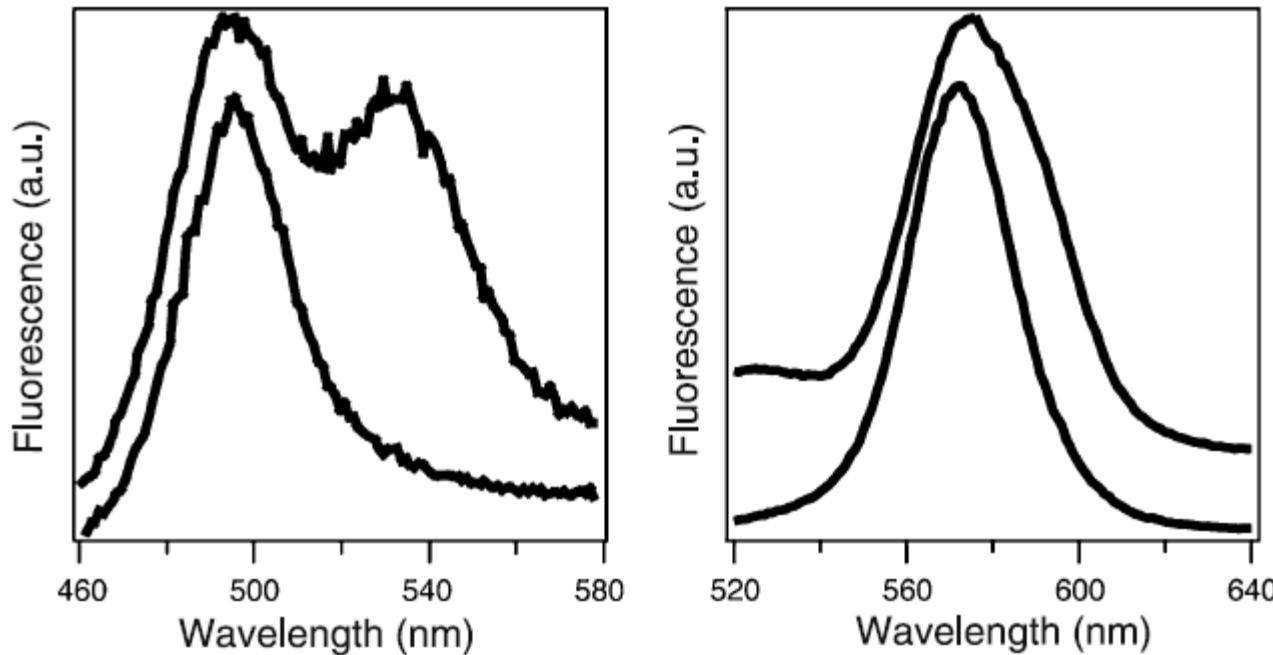
Low monomer concentration (later stage):

Large particles grow faster → defocusing (distribution broadening)

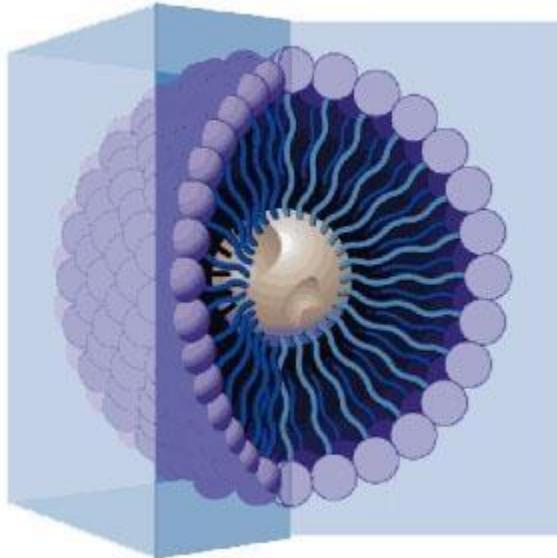
Size distribution control

- other strategies -

- Continuous monomer addition
- Size-selective precipitation:



Nanoparticles: alternative growth methods



Synthesis inside micelles

Aerosol methods

Growth termination

Spray pyrolysis

Template-based synthesis